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**REQUEST  
FOR  
CONTINUED EXAMINATION (RCE)  
TRANSMITTAL**

To Commissioner For Patents

Please enter the following submission and withdraw the finality of the proceeding office action or withdraw any pending appeal and reopen prosecution before the Examiner.

|                        |                   |
|------------------------|-------------------|
| Application Number     | 09/784,424        |
| Filing Date            | February 15, 2001 |
| First Named Inventor   | Youri Ponomarev   |
| Group Art Unit         | 2823              |
| Examiner Name          | ESTRADA, MICHELE  |
| Attorney Docket Number | NL000139          |

This is an RCE under 37 C.F.R. § 1.114 of the above-identified application (which is made prior to: payment of issue fee; abandonment; notice of appeal to the CAFC; or commencement of civil action under 35 U.S.C. 145 or 146.)

1. **Submission required under 37 C.F.R. § 1.114**

- a. ☐ Previously submitted
- i. ☐ Consider the amendment(s)/reply under 37 C.F.R. § 1.116 previously filed on \_\_\_\_\_  
(Any unentered amendment(s) referred to above will be entered).
- ii. ☐ Consider the arguments in the Appeal Brief or Reply Brief previously filed on \_\_\_\_\_
- iii. ☐ Other \_\_\_\_\_
- b. ☐ Enclosed
- i. ☐ Amendment/Reply
- ii. ☐ Affidavit(s)/Declaration(s)
- iii. ☐ Information Disclosure Statement (IDS)
- iv. ☒ Other Preliminary Amendment (may not be a brief)

2. **Miscellaneous**

- a. ☐ Suspension of action on the above-identified application is requested under 37 C.F.R. § 1.103(c) for a period of \_\_\_\_\_ months. (May not exceed 3 months; Fee required per 37 C.F.R. § 1.117(i))
- b. ☐ Other \_\_\_\_\_

3. **Fees**

- a. ☒ The Commissioner For Patents is hereby authorized to charge all required fees except the issue fee, or credit any overpayments, to Deposit Account No. 14-1270

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**SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT REQUIRED**

|                   |              |                                   |              |
|-------------------|--------------|-----------------------------------|--------------|
| Name (Print Type) | AARON WAXLER | Registration No. (Attorney/Agent) | 48,027       |
| Signature         |              | Date                              | 16 June 2003 |

**CERTIFICATE OF MAILING OR TRANSMISSION**

I hereby certify that this is being deposited with the U.S. Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner For Patents, Box RCE, Alexandria, VA 22313-1450 or facsimile transmitted to the U.S. Patent and Trademark Office tel# : \_\_\_\_\_ on the date below:

|                   |               |      |           |
|-------------------|---------------|------|-----------|
| Name (Print Type) | BURNETT JAMES | Date | 6/17/2003 |
| Signature         |               |      |           |

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#11/B  
7/15/03  
VS

Applicant: Youri Ponomarev

Atty. Docket: NL 000139

Serial No.: 09/784,424

Art Unit: 2823

Filed: February 15, 2001

Examiner: Michelle Estrada

Title: Semiconductor Device With an Integrated CMOS Circuit With MOS Transistors Having Silicon-Germanium ( $\text{Si}_{1-x}\text{Ge}_x$ ) Gate Electrodes, and Method of Manufacturing Same

Honorable Commissioner for Patents  
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Prior to calculation of the filing fee and examination, please amend the above-identified Request for Continued Examination under 37 CFR 1.114 as follows:

IN THE CLAIMS

Please amend Claim 1 as shown in marked up form in Appendix A and in clean form as follows:

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1. (Amended) A semiconductor device with an integrated CMOS circuit with NMOS and PMOS transistors having semiconductor zones which are formed in a silicon substrate and which adjoin a surface thereof, which surface is provided with a layer of gate oxide on which gate electrodes are formed at those areas of the semiconductor zones